Unit: mm

TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (U-MOS III)

TPCA8104

High-Side Switching Applications Portable Equipment Applications

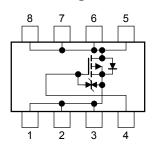
- Small footprint due to small and thin package
- Low drain-source ON-resistance: RDS (ON) = 11 m Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 50 \text{ S (typ.)}$
- Low leakage current: $IDSS = -10 \mu A (max) (VDS = -60 V)$
- Enhancement mode: V_{th} = -0.8 to -2.0 V (V_{DS} = -10 V, I_{D} = -1 mA)

⊕ 0.05 M A 0.595 0.166±0.05 △0.05 S 1, 2, 3: Source 4: Gate 5, 6, 7, 8: Drain **JEDEC** JEITA **TOSHIBA** 2-5Q1A Weight: 0.080 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Cr	naracteristic		Symbol	Rating	Unit	
Drain-source voltage			V_{DSS}	-60	V	
Drain-gate volt	tage (R _{GS} = 2	.0 kΩ)	V _{DGR} (-60	/y_	
Gate-source voltage			V _{GSS}	±20	⟨⟨v	
Drain current	DC	(Note 1)	ID((-40	A	
Dialii cuireili	Pulse	(Note 1)	IDP	-120		
Drain power di	Drain power dissipation (Tc = 25°C)			45		
Drain power dissipation (t = 10 s) (Note 2a)			PD	2.8	W	
Drain power di	ssipation (t =	10 s) (Note 2b)	PD	(1.6)	\supset	
Single-pulse avalanche energy (Note 3)			EAS	116	mJ	
Avalanche current		IAR	-40	Α		
Repetitive avalanche energy (Tc = 25°C) (Note 4)		E _{AR}	4.5	mJ		
Channel temperature		(qh	150	°C		
Storage temperature range		T _{stg}	-55 to 150	°C		

Circuit Configuration



Note: For Notes 1 to 4, see the next page.

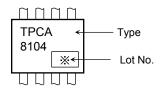
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

Characteristic	Symbol	Max	Unit	
Thermal resistance, channel to case (Tc = 25°C)	R _{th (ch-c)}	2.78	°C/W	
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	44.6	°C/W	
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1		

Marking (Note 5)



Note 1: The channel temperature should not exceed 150°C during use.

Note 2: (a) Device mounted on a glass-epoxy board (b) Device mounted on a glass-epoxy board (b)



Note 3: $V_{DD} = -24 \text{ V}$, $T_{Ch} = 25^{\circ}\text{C}$ (initial), $L \neq 0.1 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = -40 \text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature.

Note 5: * Weekly code (three digits);





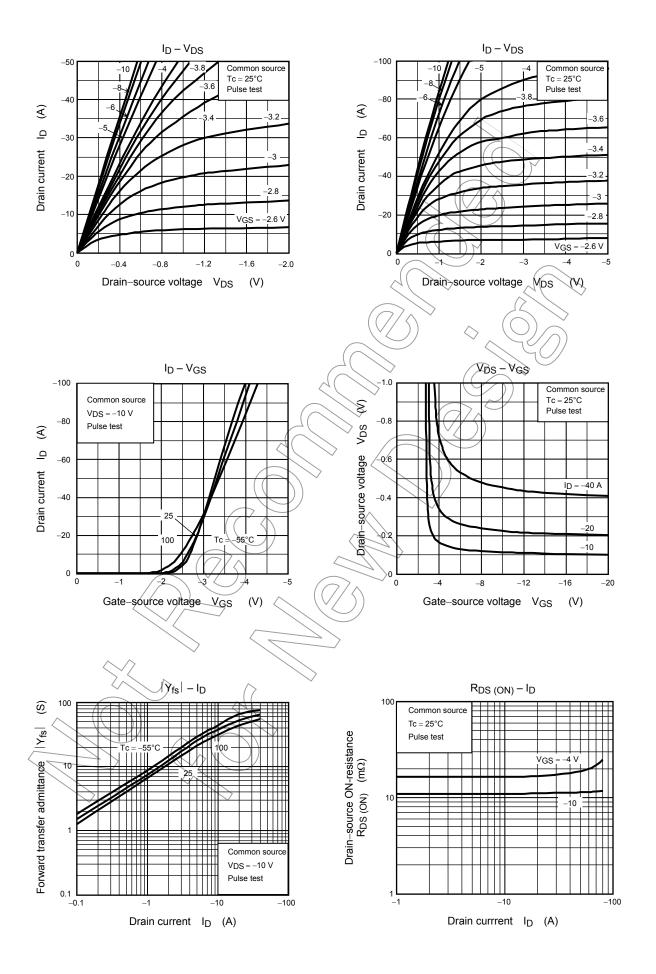
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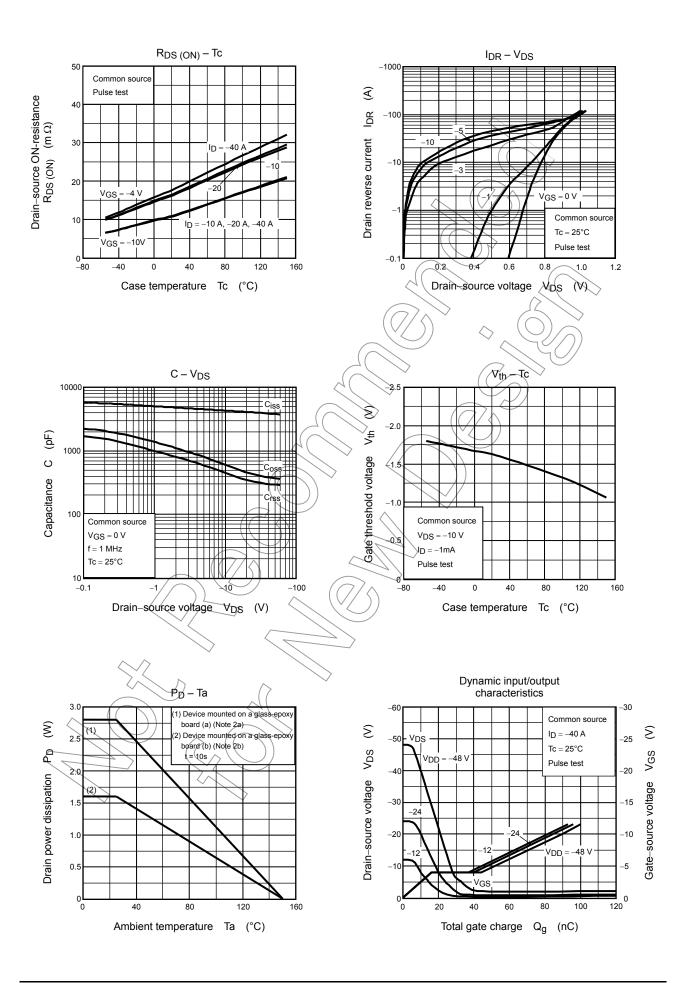
Electrical Characteristics (Ta = 25°C)

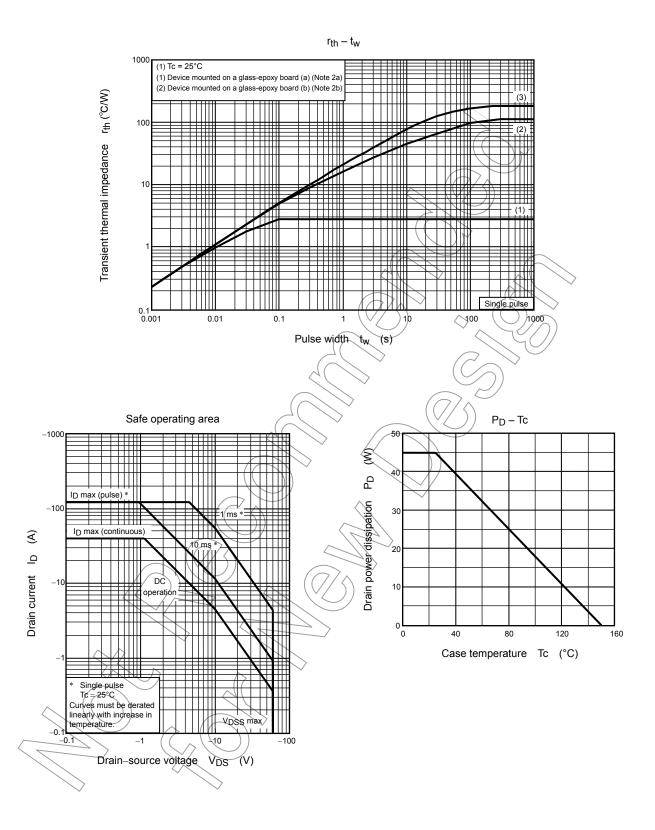
Cha	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μΑ
Drain cutoff curre	nt	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V	_	_	-10	μΑ
Drain-source breakdown voltage		V _{(BR) DSS}	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-60	_	_	٧
		V _{(BR) DSX}	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	35	_	_	
Gate threshold vo	oltage	V _{th}	V _{DS} = -10 V, I _D = -1 mA	-0.8) / _	-2.0	V
Drain source ON	raciatanaa	_	V _{GS} = -4 V, I _D = -20 A	\rightarrow	17	24	
Drain-source ON-resistance		R _{DS} (ON)	V _{GS} = -10 V, I _D = -20 A	\supset	11	16	mΩ
Forward transfer	admittance	Y _{fs}	V _{DS} = -10 V, I _D = -20 A	25	50		S
Input capacitance		C _{iss}		_	4300	_	
Reverse transfer capacitance		C _{rss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, t = 1 \text{ MHz}$	_	450	_	pF
Output capacitance		Coss			600	\searrow	
Switching time	Rise time	t _r	V _{GS} 0 V 1 1D = -20A Output	(10	> –	-
	Turn-on time	t _{on}	G \$ 1.5 G G G G G G G G G G G G G G G G G G G		> 20	_	20
	Fall time	t _f	V _{DD} ≈ (30)V/		60	_	ns
	Turn-off time	t _{off}	Duty ≤ 1%, t _W = 10 μs) _	200	_	
Total gate charge (gate-source plus gate-drain)		(Qg	V _{DD} ≈ -48 V, V _{GS} = -10 V	_	90	_	
Gate-source charge 1		Q _{gs1}	I _D = -40 A	_	16	_	nC
Gate-drain ("Miller") charge		Qgd		_	28	_	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteris	tic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	IDRP		_	_	-120	Α
Forward voltage (diode)		VDSF	I _{DR} = -40 A, V _{GS} = 0 V	_	_	1.2	V







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